Preferred Device

Small Signal MOSFET 150 mAmps, 60 Volts

N–Channel TO–92

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-------------------------------------|----------------|-------------|
| Drain-Source Voltage | VDSS | 60 | Vdc |
| Drain–Gate Voltage ($R_{GS} = 1.0 M\Omega$) | VDGR | 60 | Vdc |
| Gate–Source Voltage − Continuous − Non–repetitive (t _p ≤ 50 μs) | V _{GS} V _{GSM} | ±20 ±40 | Vdc Vpk |
| Drain Current – Continuous – Pulsed | I _D I _{DM} | 150 1000 | mAdc |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | PD | 400 3.2 | mW mW/°C |
| Operating and Storage Temperature Range | T _J , T _{stg} | –55 to +150 | °C |

THERMAL CHARACTERISTICS

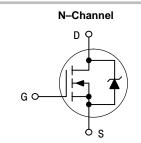
| Characteristic | Symbol | Max | Unit |
|---|-----------------|-------|------|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 312.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds | ТL | 300 | °C |



ON Semiconductor

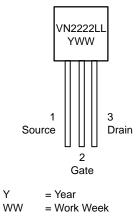
http://onsemi.com

150 mAMPS 60 VOLTS RDS(on) = 7.5 Ω





MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

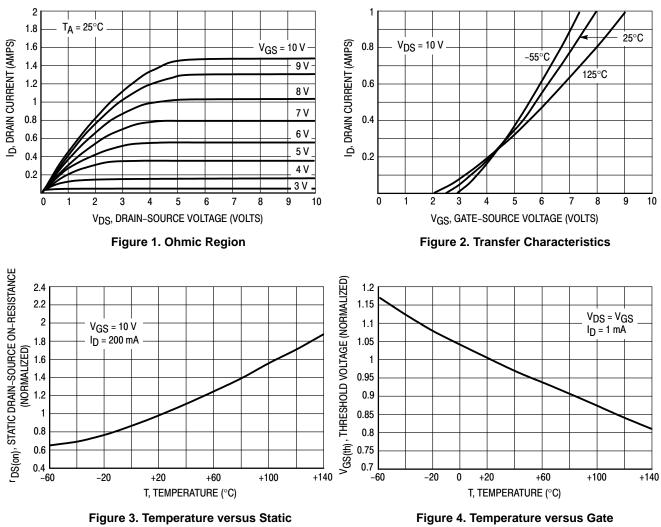
See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| Cha | Symbol | Min | Max | Unit | |
|--|---|------------------|-------------|-------|------|
| OFF CHARACTERISTICS | | | | | |
| Drain–Source Breakdown Voltage (V_{GS} = 0, I_D = 100 µAdc) | V(BR)DSS | 60 | - | Vdc | |
| Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125$ | IDSS | | 10 500 | μAdc | |
| Gate–Body Leakage Current, Forward (V _{GSF} = 30 Vdc, V _{DS} = 0) | | | - | -100 | nAdc |
| ON CHARACTERISTICS (Note 1.) | | | | 1 | • |
| Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$ | V _{GS(th)} | 0.6 | 2.5 | Vdc | |
| $\begin{array}{l} \mbox{Static Drain-Source On-Resistance} \\ (V_{GS} = 10 \mbox{ Vdc}, \mbox{ I}_{D} = 0.5 \mbox{ Adc}) \\ (V_{GS} = 10 \mbox{ Vdc}, \mbox{ I}_{D} = 0.5 \mbox{ Vdc}, \mbox{ T}_{C} = 0.5 \mbox{ Vdc}, \mbox{ V}_{C} = 0.5 \mbox{ V}_{$ | ^r DS(on) | | 7.5 13.5 | Ω | |
| $\label{eq:VGS} \begin{array}{l} \mbox{Drain-Source On-Voltage} \\ \mbox{(V}_{GS} = 5.0 \mbox{ Vdc}, \mbox{I}_{D} = 200 \mbox{ mAdc}) \\ \mbox{(V}_{GS} = 10 \mbox{ Vdc}, \mbox{I}_{D} = 500 \mbox{ mAdc}) \end{array}$ | V _{DS(on)} | _ | 1.5 3.75 | Vdc | |
| On–State Drain Current (VGS = 10 Vdc, VDS \ge 2.0 VDS(on | ID(on) | 750 | - | mA | |
| Forward Transconductance (V _{DS} = 10 Vdc, I _D = 500 mAdc) | 9fs | 100 | - | μmhos | |
| DYNAMIC CHARACTERISTICS | | | | | |
| Input Capacitance | | C _{iss} | - | 60 | pF |
| Output Capacitance | (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz) | C _{oss} | _ | 25 |] |
| Reverse Transfer Capacitance | · ··· · ·····, | C _{rss} | - | 5.0 | 1 |
| SWITCHING CHARACTERISTIC | S (Note 1.) | | | | |
| Turn–On Delay Time | (V _{DD} = 15 Vdc, I _D = 600 mA, | ton | - | 10 | ns |
| Turn–Off Delay Time | $R_{gen} = 25 \Omega, R_L = 23 \Omega$ | toff | - | 10 | 1 |

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



Drain-Source On-Resistance

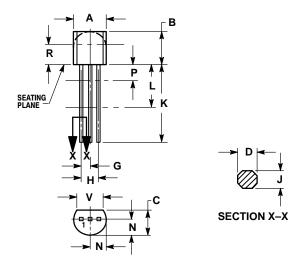
Threshold Voltage

ORDERING INFORMATION

| Device | Package | Shipping |
|------------|---------|------------------|
| VN2222LL | TO-92 | 1000 Unit/Box |
| VN2222LLRL | TO-92 | 2000 Tape & Reel |
| VN2222RLRA | TO-92 | 2000 Tape & Reel |
| VN2222RLRM | TO-92 | 1000 Unit/Box |

PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AL**



NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

CONTROLLING DIMENSION: INCH. 2 CONTOUR OF PACKAGE BEYOND DIMENSION R

3. IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND

BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIMETER | |
|-----|--------|-------|------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| Ρ | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| V | 0.135 | | 3.43 | |

STYLE 22: PIN 1. SOURCE 2. GATE 3 DRAIN

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JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031 Phone: 81-3-5740-2700 Email: r14525@onsemi.com

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